

**100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT23F**
**Features**

- $BV_{CEO} > 100V$
- $BV_{CEX} > 200V$
- $BV_{ECO} > 5V$
- $I_C = 4.5A$  Continuous Collector Current
- Low Saturation Voltage  $V_{CE(SAT)} < 60mV @ 1A$
- $R_{CE(SAT)} = 38m\Omega$
- $h_{FE}$  Characterised Up to 5A
- 1.5W Power Dissipation
- Complementary PNP Type: ZXTP19100CFF
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Description**

Advanced process capability has been used to maximise the performance of this transistor. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

**Mechanical Data**

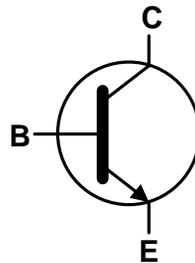
- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.012 grams (Approximate)

**Applications**

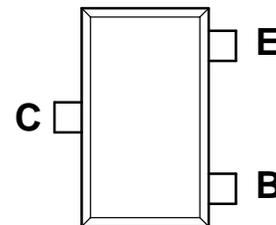
- Line Switching
- Motor Driving (Including DC Fans)
- High-Side Switches
- Subscriber Line Interface Cards (SLIC)



Top View



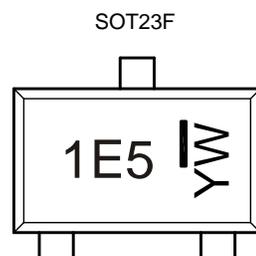
Device Symbol


 Top View  
Pin Configuration

**Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19100CFFTA	AEC-Q101	1E5	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**


- 1E5 = Product Type Marking Code  
 YW = Date Code Marking  
 Y = Year : 0~9  
 W = Week : A~Z : 1~26  
           a~z : 27~52  
           z represents 52 & 53 week

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage (Forward Blocking)	V <sub>CEX</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Collector Voltage (Reverse Blocking)	V <sub>ECO</sub>	5	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	4.5	A
Peak Pulse Current	I <sub>CM</sub>	6	A
Base Current	I <sub>B</sub>	1	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

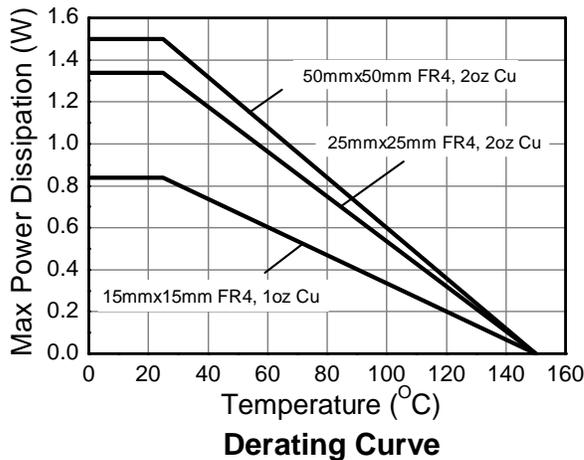
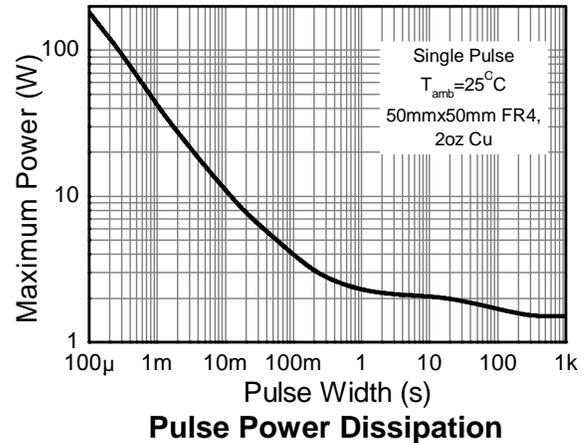
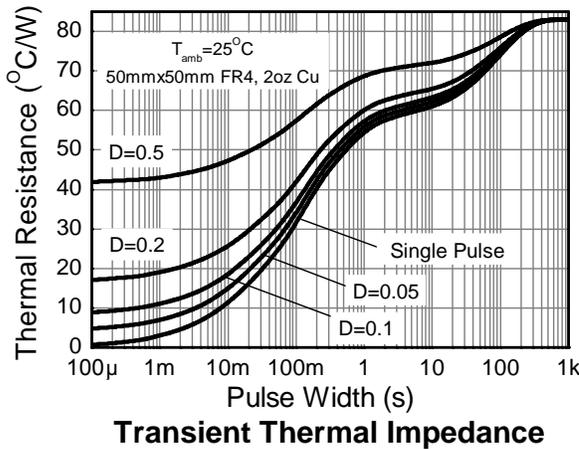
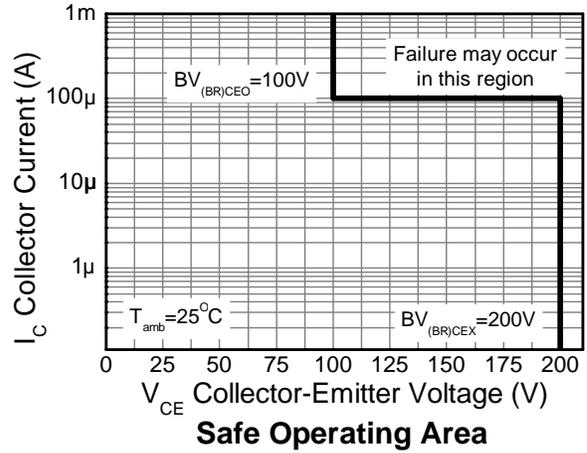
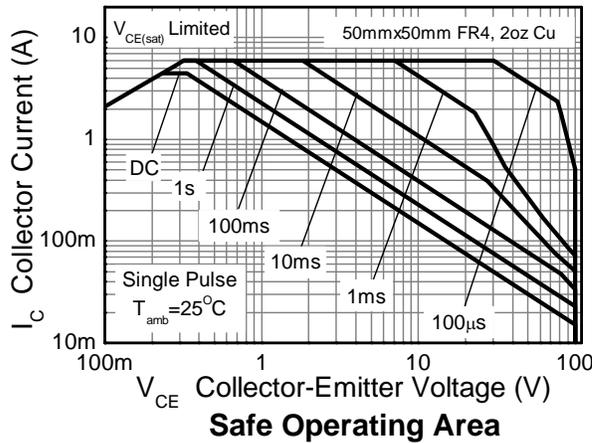
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P <sub>D</sub>	0.84	W mW/°C
		6.72	
		1.34	
		10.72	
		1.50	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	12.0	°C/W
		2.0	
		16.0	
		149	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	93	°C/W
		83	
		60	
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	43.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
  - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
  - Same as Note 7, whilst measured at t < 5 seconds.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

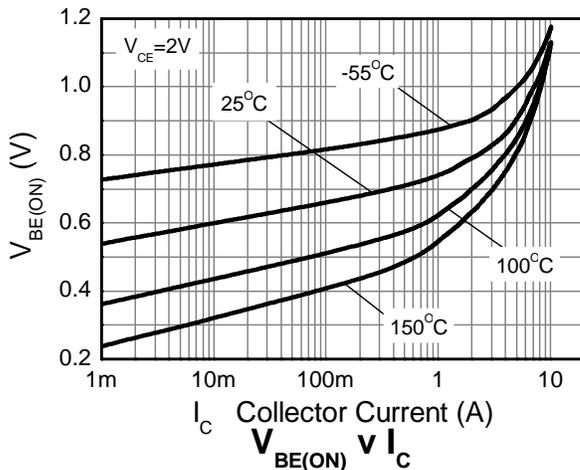
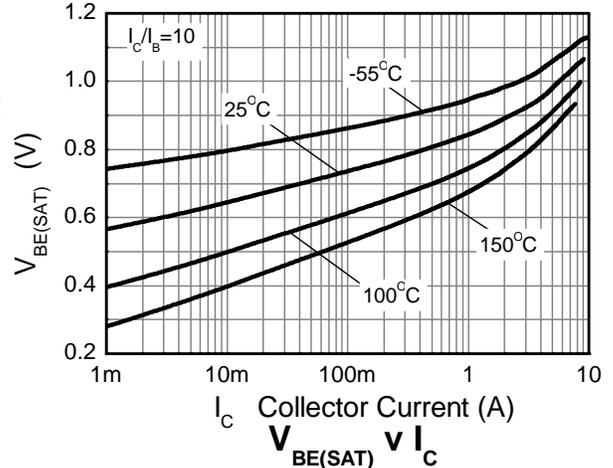
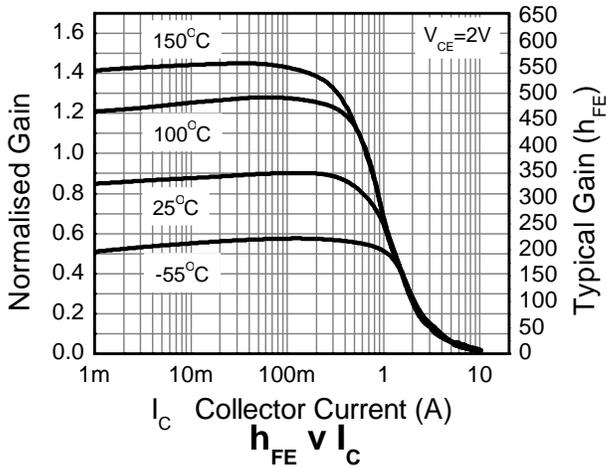
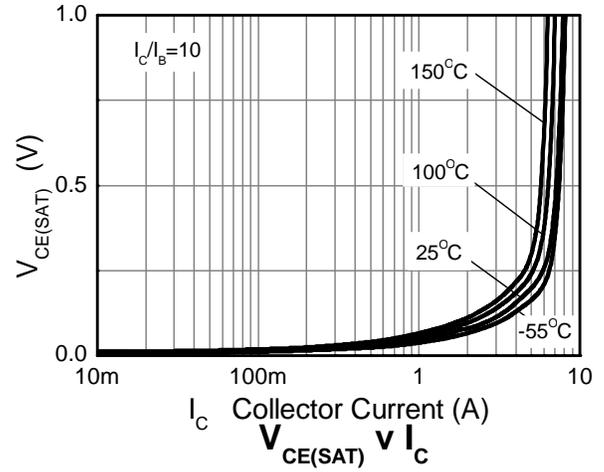
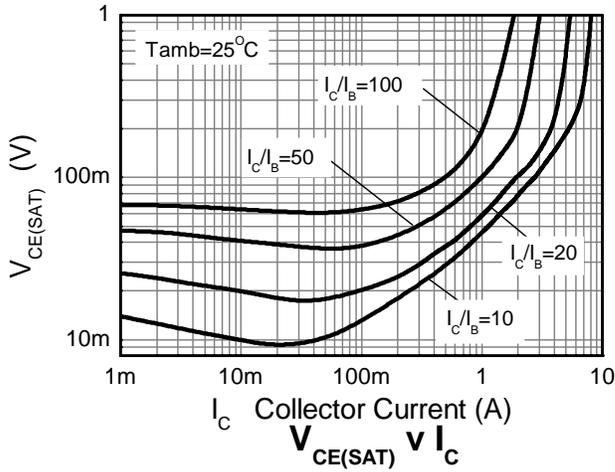


**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	200	240	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Forward Blocking)	$BV_{CEX}$	200	240	—	V	$I_C = 100\mu\text{A}$ , $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	$BV_{CEO}$	100	120	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7	8.3	—	V	$I_E = 100\mu\text{A}$
Emitter-Collector Breakdown Voltage (Reverse Blocking)	$BV_{ECX}$	6	8.3	—	V	$I_E = 100\mu\text{A}$ , $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} < V_{BC} < -0.25\text{V}$
Emitter-Collector Breakdown Voltage (Base Open)	$BV_{ECO}$	5	8	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	$I_{CBO}$	—	<1	50	nA $\mu\text{A}$	$V_{CB} = 160\text{V}$ $V_{CB} = 160\text{V}$ , $T_A = +100^\circ\text{C}$
Emitter-Base Cutoff Current	$I_{EBO}$	—	<1	50	nA	$V_{EB} = 5.6\text{V}$
<b>ON CHARACTERISTICS</b> (Note 11)						
Static Forward Current Transfer Ratio	$h_{FE}$	200 130 —	350 250 25	500 — —	—	$I_C = 100\text{mA}$ , $V_{CE} = 2\text{V}$ $I_C = 1\text{A}$ , $V_{CE} = 2\text{V}$ $I_C = 5\text{A}$ , $V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	45 105 170	60 135 235	mV	$I_C = 1\text{A}$ , $I_B = 100\text{mA}$ $I_C = 1\text{A}$ , $I_B = 20\text{mA}$ $I_C = 4.5\text{A}$ , $I_B = 450\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	950	1050	mV	$I_C = 4.5\text{A}$ , $I_B = 450\text{mA}$
Base-Emitter On Voltage	$V_{BE(ON)}$	—	880	1000	mV	$I_C = 4.5\text{A}$ , $V_{CE} = 2\text{V}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	$f_T$	—	150	—	MHz	$I_C = 100\text{mA}$ , $V_{CE} = 10\text{V}$ , $f = 50\text{MHz}$
Input Capacitance	$C_{IBO}$	—	305	—	pF	$V_{EB} = 0.5\text{V}$ , $f = 1\text{MHz}$
Output Capacitance	$C_{OBO}$	—	15.7	25	pF	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}$
Delay Time	$t_D$	—	28.3	—	ns	$V_{CC} = 10\text{V}$ , $I_C = 500\text{mA}$ , $I_{B1} = I_{B2} = 50\text{mA}$
Rise Time	$t_R$	—	23.6	—	ns	
Storage Time	$t_S$	—	962	—	ns	
Fall Time	$t_F$	—	133	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$

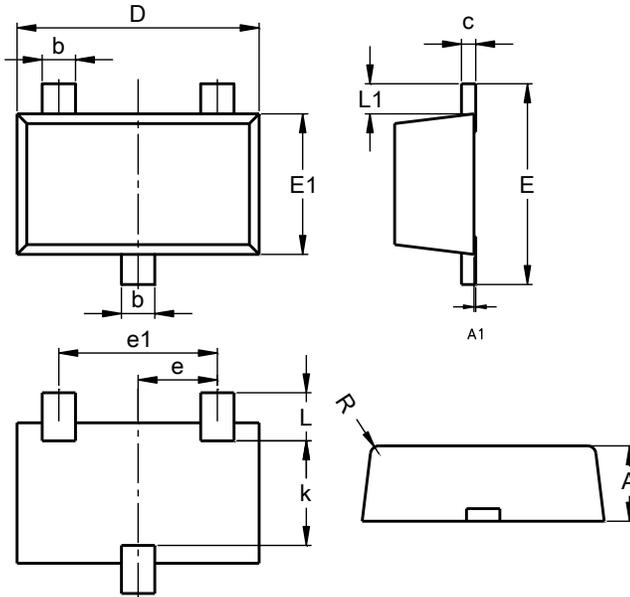
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



**Package Outline Dimensions**

Please see AP02001 at [http://www.diodes.com/\\_files/datasheets/ap02001.pdf](http://www.diodes.com/_files/datasheets/ap02001.pdf) for the latest version.

**SOT23F**

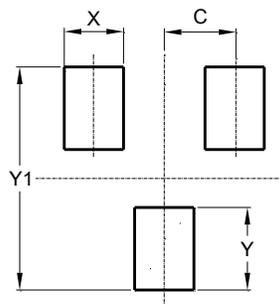


SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	0.190 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at [http://www.diodes.com/\\_files/datasheets/ap02001.pdf](http://www.diodes.com/_files/datasheets/ap02001.pdf) for the latest version.

**SOT23F**



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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